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Hierarchical 1T-MoS₂ Nanotubular Structures for Enhanced

Supercapacitive Performance

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Fig. S1 (a) SEM image and (b) XRD pattern of the as-prepared MoO₃ nanobelts.



Fig. S2 (a) SEM image of the as-prepared 1T-MoS $_2$; (b) XRD patterns of as-prepared 1T-MoS $_2$ and annealed 1T-MoS $_2$.



Fig. S3 S 2p XPS spectrums of as-prepared 1T-MoS₂ and annealed 1T-MoS₂.



Fig. S4 Fitting curves for EXAFS data of the Mo K-edge for commercial MoS_2 , annealed $1T-MoS_2$ and as-prepared $1T-MoS_2$.



Fig. S5 (a) Nitrogen adsorption-desorption isotherm and (b) pore diameter distribution of as-prepared 1T-MoS₂, annealed 1T-MoS₂ and commercial MoS₂.



Fig. S6 (a) Specific capacitances for a current density range from 6 to 15 A g⁻¹, (b) CV curves for a scan rate range from 100 to 1000 mV s⁻¹, and (c) GCD profile for a current density range from 6 to 10 A g⁻¹ for the as-prepared 1T-MoS₂ tested in a three-electrode system.



Fig. S7 (a) Specific capacitances for a current density range from 6 to 15 A g⁻¹, (b) CV curves for a scan rate range from 100 to 1000 mV s⁻¹, and (c) GCD profiles for a current density range from 6 to 10 A g⁻¹ for the as-prepared 1T-MoS₂ tested in a two-electrode system.



Fig. S8 CV curves and GCD profiles for the (a, b) annealed 1T-MoS₂, and (c, d) commercial MoS₂, measured using a three-electrode system.



Fig. S9 CV curves and GCD profiles for the (a, b) annealed 1T-MoS₂, and (c, d) commercial MoS₂, measured using a two-electrode symmetrical cell.

Table S1 Local structural parameters for Mo and S atoms in commercial MoS2,annealed 1T-MoS2 and as-prepared 1T-MoS2 fitted from EXAFS data. R is the lengthof bond, N is the coordination number and σ^2 is Debye-Waller factor.

Sample	Path	R (Å)	Ν	σ² (10 ⁻³ Å)
Commercial MoS ₂	Mo-S	2.41	6	3.6
	Mo-Mo	1.37	6	3.1
Annealed 1T-MoS ₂	Mo-S	2.41	4.7	3.7
	Mo-Mo	3.16	3.7	5.4
1T-MoS ₂	Mo-S	2.38	3.8	9.2
	Mo-Mo	2.76	1.5	10.7

Table S2 Synthesis conditions and specific capacitances comparisons of variousmaterials reported from references with our obtained 1T- MoS2.

Materials	Synthesis Method	Specific Capacitance	Electrolyte	Ref.
MoS ₂ nanosheet	Hydrothermal	129.2 F/g (1 A/g)	1 M Na ₂ SO ₄	1
MoS ₂ nanosheet	Hydrothermal	8 mF/cm ²	$1 \text{ M Na}_2 \text{SO}_4$	2
MoS ₂ nanosheet	Hydrothermal	92 F/g (0.5 mA/cm ²)	1 M Na ₂ SO ₄	3
MoS ₂ nanosphere	Hydrothermal	122 F/g (1 A/g)	1 M KCl	4
2D MoS₂ on graphene oxide	Microwave Heating	265 F/g (10 mV/s)	1 M HClO ₄	5
Flower-like MoS ₂	Hydrothermal	168 F/g (1 A/g)	1 M KCl	6
MoS₂ nanosheet on Mo foil	Hydrothermal	192.7 F/g (1 mA/cm²)	$1 \text{ M Na}_2 \text{SO}_4$	7
MoS ₂ nanosheet	Solvothermal	231 F/g (1 A/g)	$1 \text{ M Na}_2 \text{SO}_4$	8
MoS ₂ nanosheet	Solvothermal	348 F/g (1 A/g)	$1 \text{ M H}_2\text{SO}_4$	This work

Materials	Synthesis Method	Specific Capacitance	Electrolyte	Ref.
CoS ₂	Microwave- mediated	119 F/g (1 A/g)	1 M LiPF ₆ - based	9
CoS ₂	Hydrothermal	236.5 F/g (1A/g)	2 M KOH	10
NiS ₂ /NiS	Hydrothermal	717 F/g (0.6 A/g)	3 М КОН	11
NiS ₂	Microwave- assisted	695 F/g (1.25 A/g)	3 М КОН	12
NiS ₂ /graphene	Solvothermal	426 F/g (1A/g)	6 M KOH	13
MnS ₂	Hydrothermal	471 F/g (0.5 mA/cm²)	-	14
SnS ₂	Solvothermal	216 F/g (0.38 A/g)	1 M KCl	15
WS ₂	Hydrothermal	2813 μF/g (0.5 A/m²)	$1 \text{ M H}_2\text{SO}_4$	16
VS ₂	Chemical exfoliating	4760 μF /cm² (0.1 A/m²)	BM1MBF ₄ - PVA	17
VS ₂	Hydrothermal	155 F/g (1 mA/cm ²)	6 М КОН	18
MoS ₂ nanosheet	Solvothermal	348 F/g (1 A/g)	1 M H ₂ SO ₄	This work

Table S3 Synthesis conditions and specific capacitances comparisons of various metal disulfides reported from references with our obtained 1T- MoS₂.

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